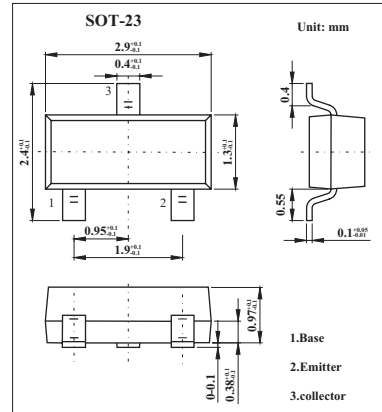


■ Features

- Micro package.
- High dc current gain. hFE:200TYP. (VCE=1V, IC=100mA)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V <sub>CB0</sub>	30	V
Collector to emitter voltage	V <sub>CEO</sub>	25	V
Emitter to base voltage	V <sub>EB0</sub>	5	V
Collector current (DC)	I <sub>C</sub>	700	mA
Total power dissipation	P <sub>T</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0			100	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0			100	nA
DC current gain *	h <sub>FE</sub>	V <sub>CE</sub> = 1.0 V, I <sub>C</sub> = 100 mA	110	200	400	
Base to emitter voltage *	V <sub>BE</sub>	V <sub>CE</sub> = 6.0 V, I <sub>C</sub> = 10 mA	600	640	700	mV
Collector saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> = 700 mA, I <sub>B</sub> = 70 mA		0.22	0.6	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 6.0 V, I <sub>E</sub> = 0, f = 10 MHz		12		pF
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = 6.0 V, I <sub>E</sub> = -10 mA		170		MHz

\* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ hFE Classification

Marking	DV				
Rank	1	2	3	4	5
hFE	110~180	135~220	170~270	200~320	250~400